IXYS

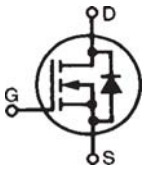
Advance Technical Information

High Voltage Power MOSFET

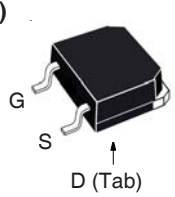
IXTT1N450HV

V_{DSS} = 4500V
I_{D25} = 1A
$R_{DS(on)}$ ≤ 85Ω

N-Channel Enhancement Mode



TO-268 (IXTT)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	4500	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	4500	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	1	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	3	A
P_D	T_C = 25°C	520	W
T_J		- 55 ... +150	°C
T_{JM}		150	°C
T_{stg}		- 55 ... +150	°C
T_L	1.6mm (0.062 in.) from Case for 10s	300	°C
T_{SOLD}	Plastic Body for 10 seconds	260	°C
Weight		4	g

Features

- High Blocking Voltage
- High Voltage Package

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits
- Laser and X-Ray Generation Systems

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	4.0		6.5	V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
I_{DSS}	V_{DS} = 3.6kV, V_{GS} = 0V			10	μA
	V_{DS} = 4.5kV			50	μA
	V_{DS} = 3.6kV T_J = 100°C		25		μA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 50mA, Note 1			85	Ω

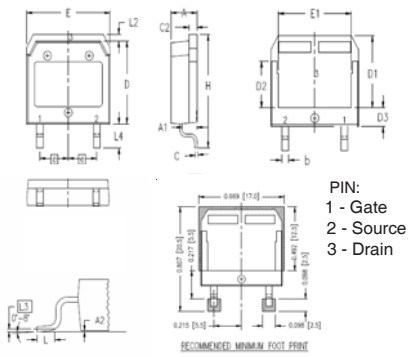
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 50V, I_D = 200mA, Note 1	0.28	0.46		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		1730		pF
C_{oss}			78		pF
C_{rss}			28		pF
R_{Gi}	Gate Input Resistance		21		Ω
$t_{d(on)}$	**Resistive Switching Times**		34		ns
t_r	V_{GS} = 10V, V_{DS} = 500V, I_D = 0.5 • I_{D25}		60		ns
$t_{d(off)}$	R_G = 10Ω (External)		58		ns
t_f			127		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 1kV, I_D = 0.5 • I_{D25}		40		nC
Q_{gs}			10		nC
Q_{gd}			20		nC
R_{thJC}				0.24	°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			1	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			5	A
V_{SD}	I_F = 1A, V_{GS} = 0V, Note 1			2.0	V
t_{rr}	I_F = 1A, -di/dt = 50A/μs, V_R = 100V		1.75		μs

Note: 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

TO-268 (VHV) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETER MIN	MILLIMETER MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

Fig. 1. Output Characteristics @ T_J = 25ºC

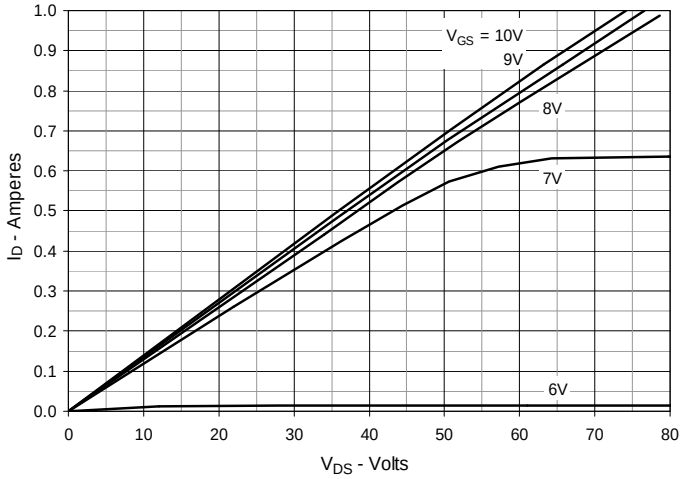


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

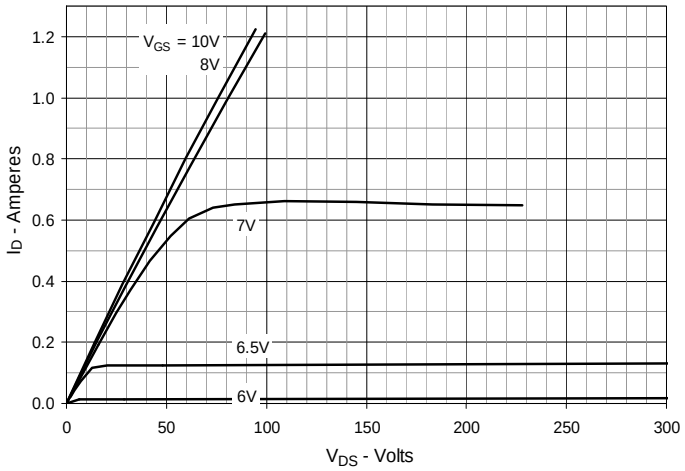


Fig. 3. Output Characteristics @ T_J = 125ºC

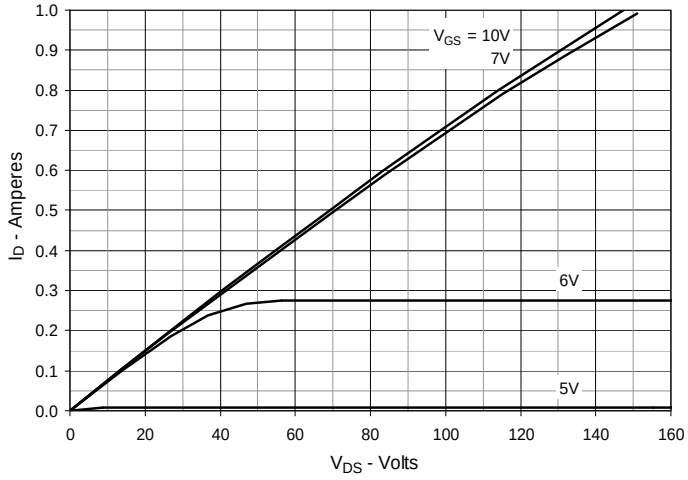


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 0.5A Value vs. Junction Temperature

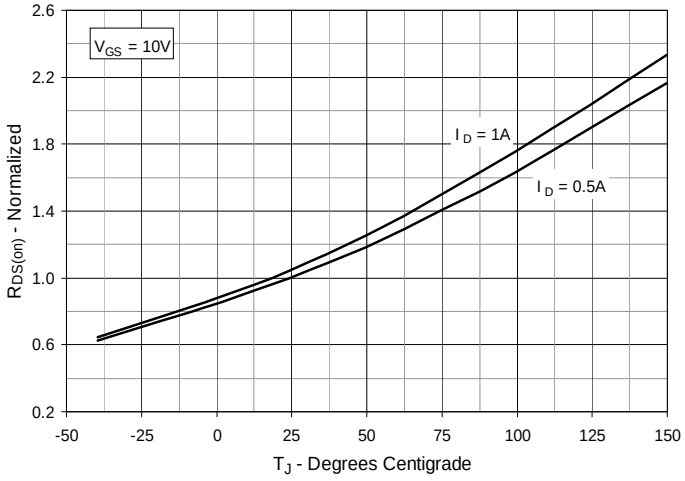


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 0.5A Value vs. Drain Current

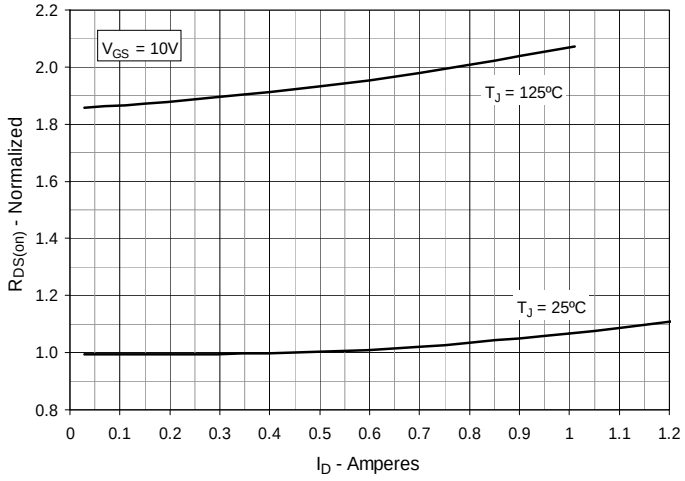


Fig. 6. Maximum Drain Current vs. Case Temperature

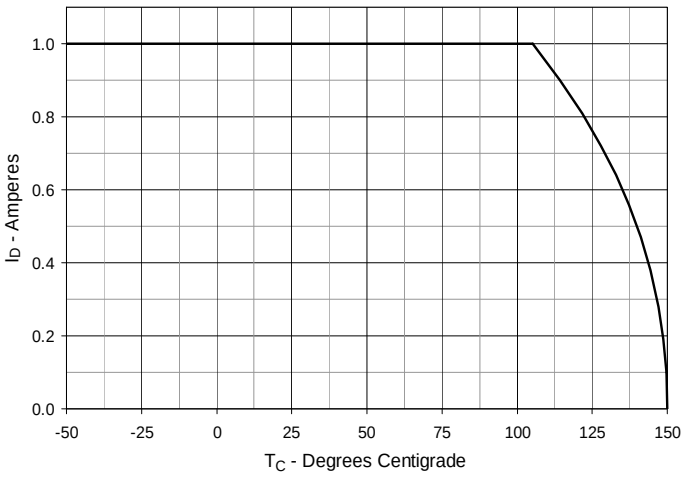


Fig. 7. Input Admittance

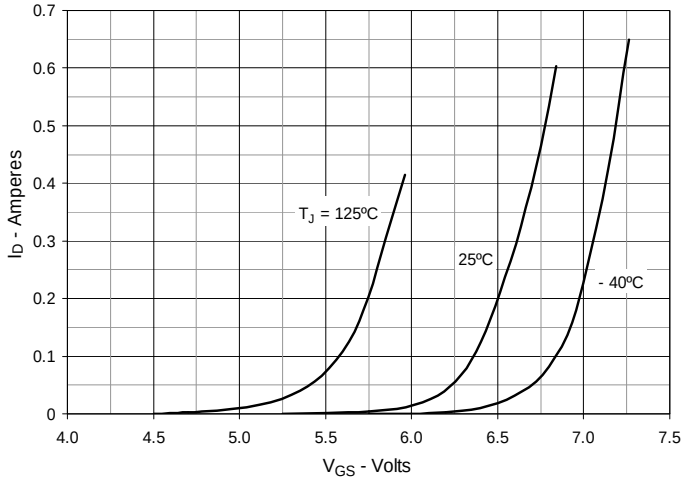


Fig. 8. Transconductance

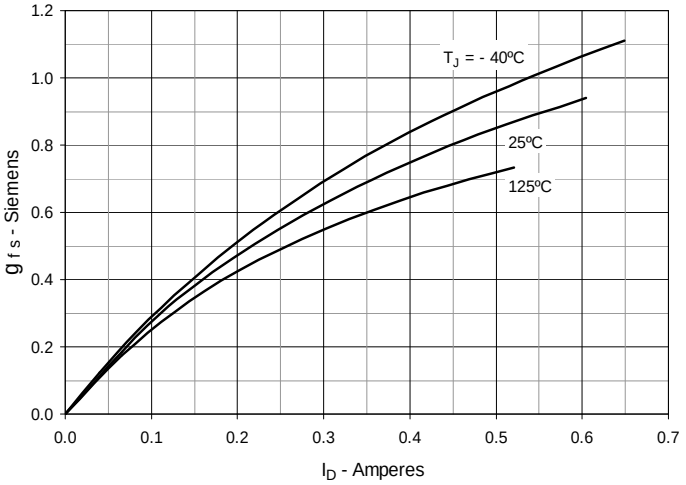


Fig. 9. Forward Voltage Drop of Intrinsic Diode

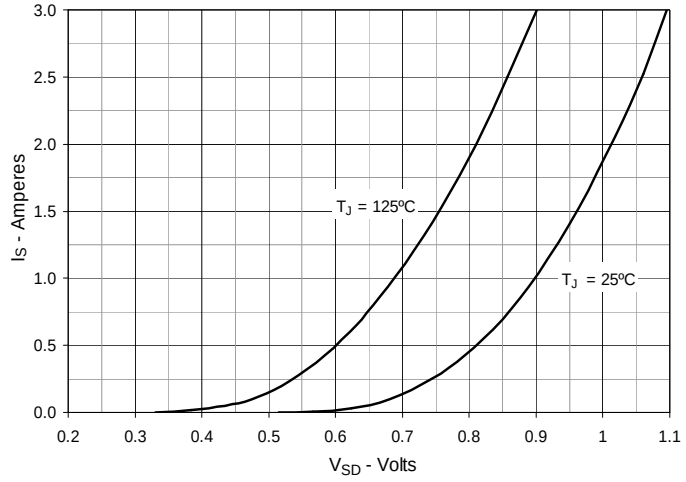


Fig. 10. Gate Charge

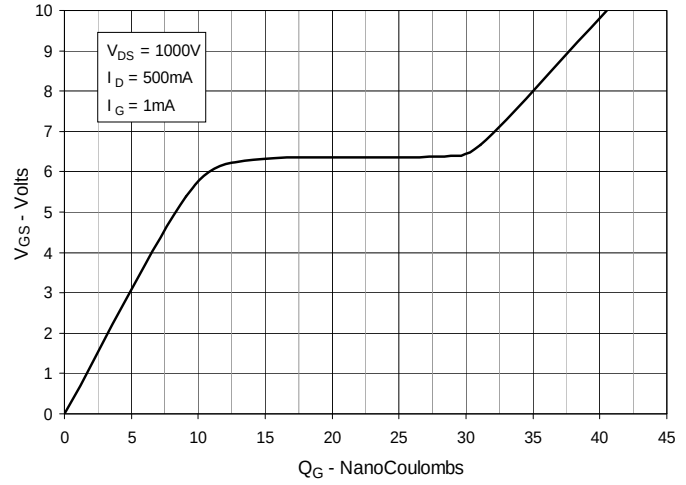


Fig. 11. Capacitance

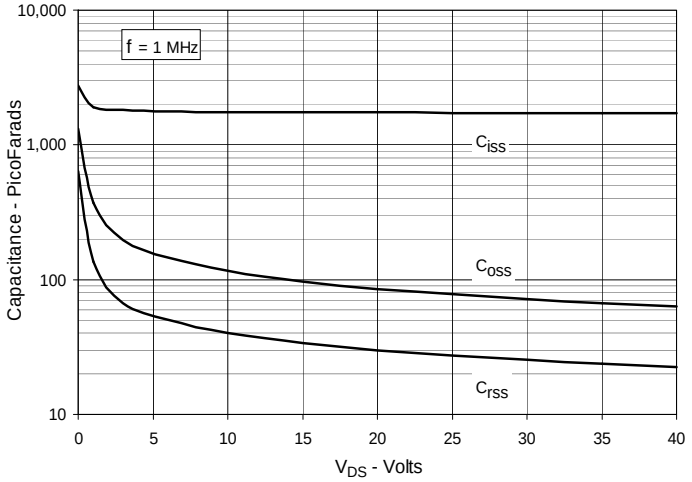


Fig. 12. Maximum Transient Thermal Impedance

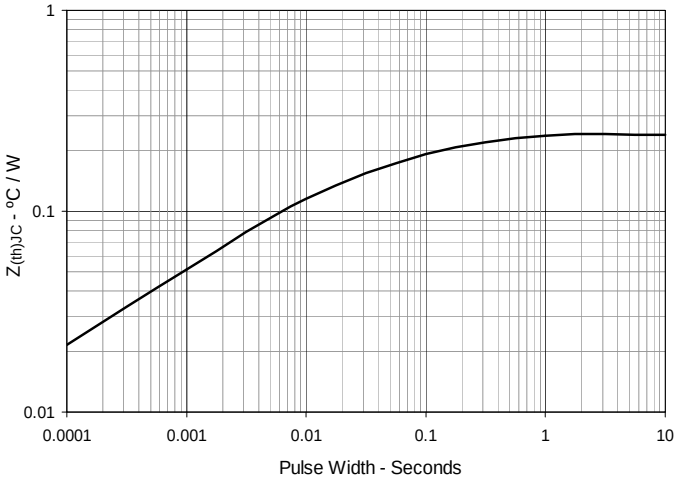


Fig. 13. Forward-Bias Safe Operating Area @ T_C = 25ºC

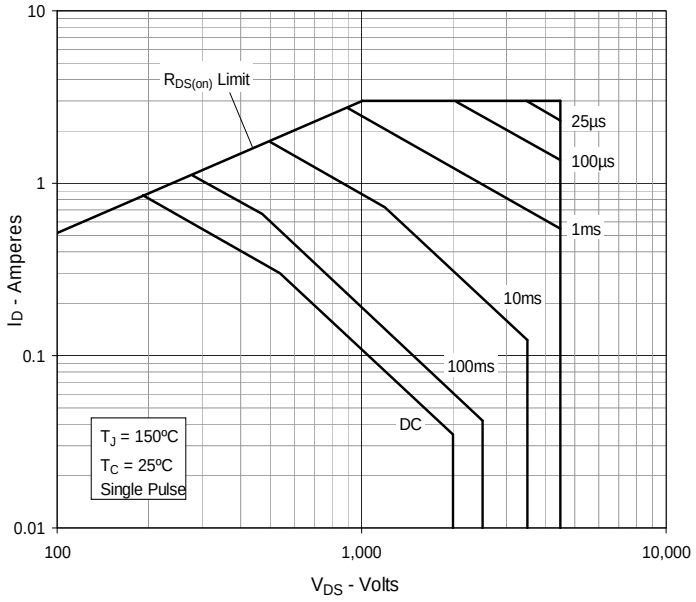


Fig. 14. Forward-Bias Safe Operating Area @ T_C = 75ºC